



**CHENMKO ENTERPRISE CO.,LTD**

*Lead free devices*

**SURFACE MOUNT  
Dual Silicon Transistor**

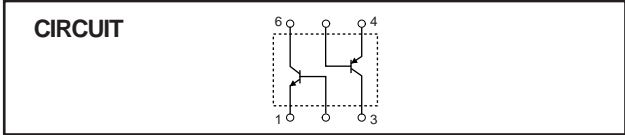
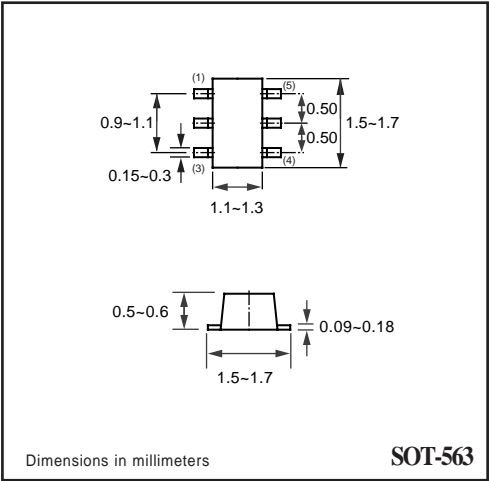
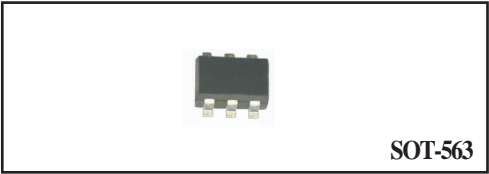
VOLTAGE 15 Volts CURRENT 500 mAmpere

**CHEMZ7PT**

**APPLICATION**  
\* Small Signal Amplifier .

**FEATURE**  
\* Small surface mounting type. (SOT-563)  
\* Low saturation voltage  $V_{CE(sat)}=0.25V(max.)$ ( $I_c=200mA$ )  
\* Low cob.  $C_{ob}=7.5pF(Typ.)$   
\*  $P_c= 150mW$  (Total),120mW per element must not be exceeded.  
\* High saturation current capability.  
\* Both the 2SC5585 & 2SA2018 in one package.  
\* NPN / PNP Silicon Transistor

**MARKING**  
\* Z7



**2SC5585 LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL    | PARAMETER                 | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|------------|------|------|------|
| $V_{CBO}$ | Collector-base voltage    |            | –    | 15   | V    |
| $V_{CEO}$ | Collector-emitter voltage |            | –    | 12   | V    |
| $V_{EBO}$ | Emitter-base voltage      |            | –    | 6    | V    |
| $I_c$     | DC Output current         |            | –    | 500  | mA   |
| $I_{cp}$  |                           | NOTE.1     | –    | 1000 |      |
| $P_c$     | Total power dissipation   | NOTE.2     | –    | 150  | mW   |
| $T_{STG}$ | Storage temperature       |            | –55  | +150 | °C   |
| $T_J$     | Junction temperature      |            | –    | 150  | °C   |

**Note**

- Single pulse  $P_w=1ms$
- 120mW per element must not be exceeded.  
Each terminal mounted on a recommended land.

**2SA2018 LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                 | CONDITIONS | MIN. | MAX.  | UNIT |
|------------------|---------------------------|------------|------|-------|------|
| V <sub>CB0</sub> | Collector-base voltage    |            | -    | -15   | V    |
| V <sub>CE0</sub> | Collector-emitter voltage |            | -    | -12   | V    |
| V <sub>EBO</sub> | Emitter-base voltage      |            | -    | -6    | V    |
| I <sub>C</sub>   | DC Output current         |            | -    | -500  | mA   |
| I <sub>CP</sub>  |                           | NOTE.1     | -    | -1000 |      |
| P <sub>c</sub>   | power dissipation         |            | -    | 150   | mW   |
| T <sub>STG</sub> | Storage temperature       |            | -55  | +150  | °C   |
| T <sub>J</sub>   | Junction temperature      |            | -    | 150   | °C   |

**Note**

1. Single Pulse Pw=1ms

**2SC5585 CHARACTERISTICS**T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL               | PARAMETER                            | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| BV <sub>CEO</sub>    | Collector-emitter breakdown voltage  | I <sub>c</sub> =1mA                                  | 12   | -    | -    | V    |
| BV <sub>CB0</sub>    | Collector-base breakdown voltage     | I <sub>c</sub> =10uA                                 | 15   | -    | -    | V    |
| BV <sub>EBO</sub>    | Emitter-base breakdown voltage       | I <sub>E</sub> =10uA                                 | 6    | -    | -    | V    |
| I <sub>CB0</sub>     | Collector cut-off current            | V <sub>CB</sub> =15V                                 | -    | -    | 100  | nA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =6V                                  | -    | -    | 100  | nA   |
| h <sub>FE</sub>      | DC current gain                      | V <sub>CE</sub> =2V, I <sub>c</sub> =10mA            | 270  | -    | 680  | -    |
| V <sub>CE(sat)</sub> | Collector-emitter saturation voltage | I <sub>c</sub> =200mA, I <sub>B</sub> =10mA          | -    | 90   | 250  | mV   |
| C <sub>ob</sub>      | Collector output capacitance         | V <sub>CB</sub> =10V, I <sub>E</sub> =0mA, f=1MHZ    | -    | 7.5  | -    | pF   |
| f <sub>T</sub>       | Transition frequency                 | V <sub>CE</sub> =2V, I <sub>E</sub> =-10mA, f=100MHZ | -    | 320  | -    | MHz  |

**2SA2018 CHARACTERISTICS**T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL               | PARAMETER                            | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| BV <sub>CEO</sub>    | Collector-emitter breakdown voltage  | I <sub>c</sub> =-1mA                                 | -12  | -    | -    | V    |
| BV <sub>CB0</sub>    | Collector-base breakdown voltage     | I <sub>c</sub> =-10uA                                | -15  | -    | -    | V    |
| BV <sub>EBO</sub>    | Emitter-base breakdown voltage       | I <sub>E</sub> =-10uA                                | -6   | -    | -    | V    |
| I <sub>CB0</sub>     | Collector cut-off current            | V <sub>CB</sub> =-15V                                | -    | -    | -100 | nA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-6V                                 | -    | -    | -100 | nA   |
| h <sub>FE</sub>      | DC current gain                      | V <sub>CE</sub> =-2V, I <sub>c</sub> =-10mA          | 270  | -    | 680  | -    |
| V <sub>CE(sat)</sub> | Collector-emitter saturation voltage | I <sub>c</sub> =-200mA, I <sub>B</sub> =-10mA        | -    | -100 | -250 | mV   |
| C <sub>ob</sub>      | Collector output capacitance         | V <sub>CB</sub> =-10V, I <sub>E</sub> =0mA, f=1MHZ   | -    | 6.5  | -    | pF   |
| f <sub>T</sub>       | Transition frequency                 | V <sub>CE</sub> =-2V, I <sub>E</sub> =10mA, f=100MHZ | -    | 260  | -    | MHz  |

## RATING CHARACTERISTIC CURVES ( CHEMZ7PT )

### 2SC5585 Typical Electrical Characteristics

Fig.1 Ground emitter propagation characteristics

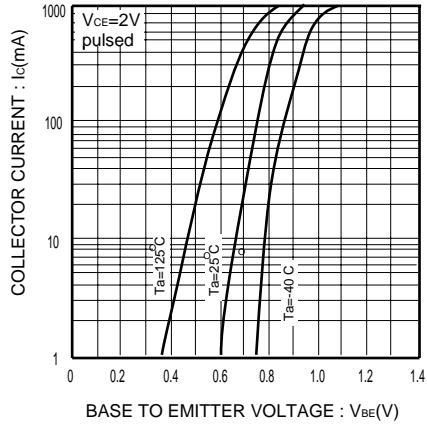


Fig.2 DC current gain vs. collector current

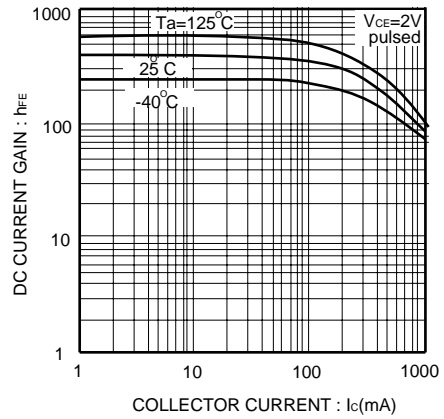


Fig.3 Collector-emitter saturation voltage vs. collector current ( I )

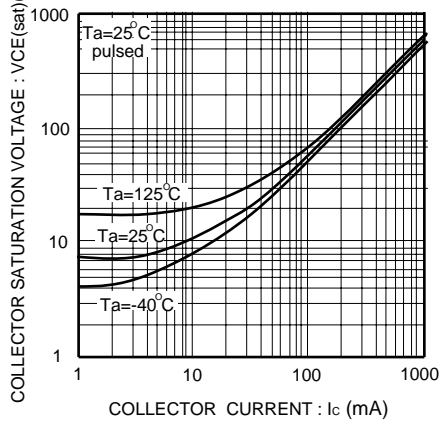
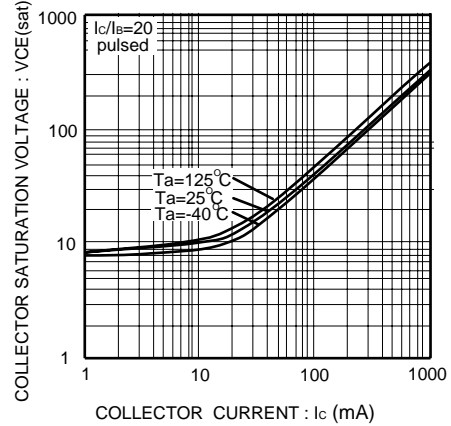


Fig.4 Collector-emitter saturation voltage vs. collector current ( II )



## RATING CHARACTERISTIC CURVES ( CHEMZ7PT )

### 2SC5585 Typical Electrical Characteristics

Fig.5 Base-emitter saturation voltage vs. collector current

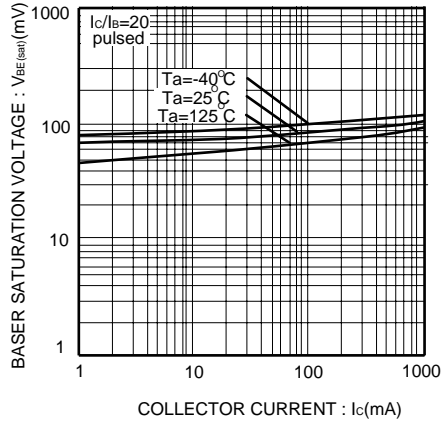


Fig.6 Gain bandwidth product vs. collector current

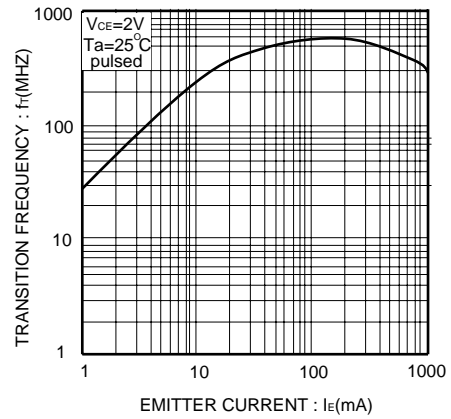
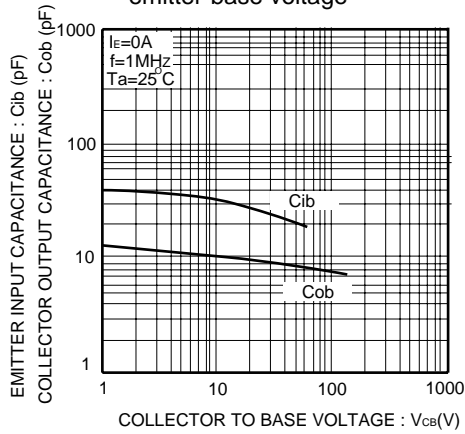


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage



## RATING CHARACTERISTIC CURVES ( CHEMZ7PT )

### 2SA2018 Typical Electrical Characteristics

Fig.1 Ground emitter propagation characteristics

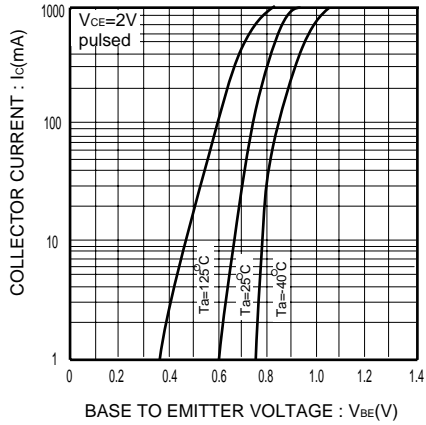


Fig.2 DC current gain vs. collector current

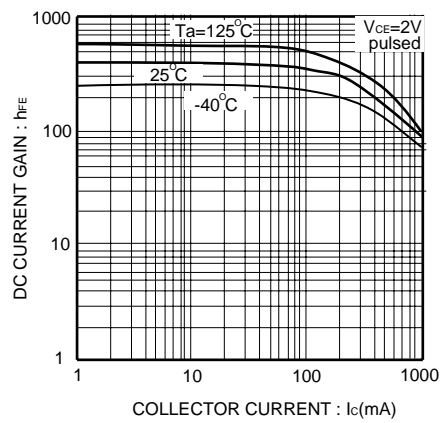


Fig.3 Collector-emitter saturation voltage vs. collector current ( I )

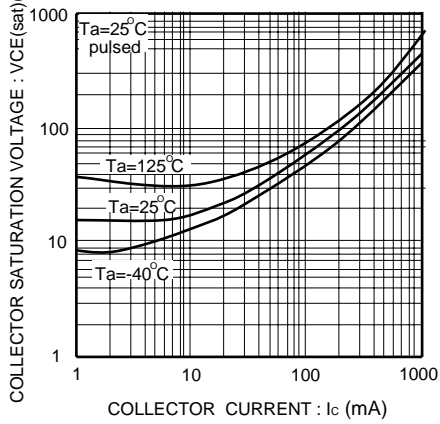
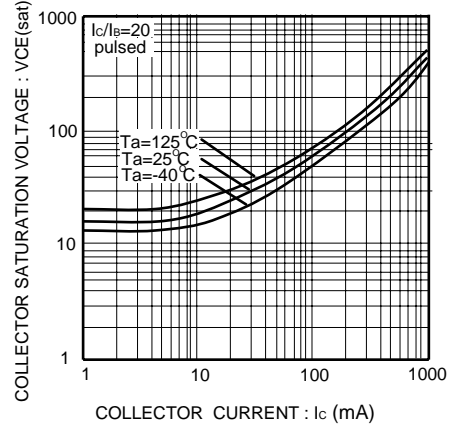


Fig.4 Collector-emitter saturation voltage vs. collector current ( II )



## RATING CHARACTERISTIC CURVES ( CHEMZ7PT )

### 2SA2018 Typical Electrical Characteristics

Fig.5 Base-emitter saturation voltage vs. collector current

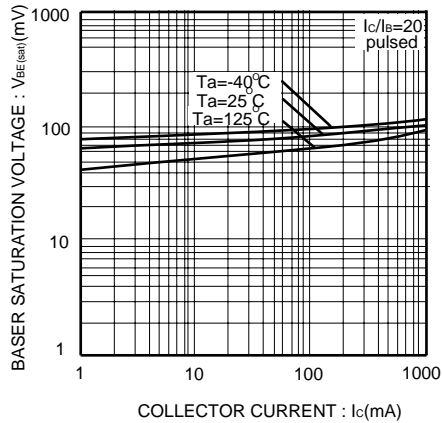


Fig.6 Gain bandwidth product vs. collector current

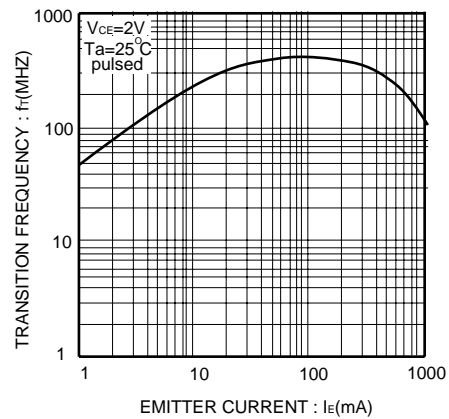


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

